

**Features:**

- Isolated mounting base 3000V~
- Solder joint technology with increased power cycling capability
- Space and weight saving

Typical Applications:

- AC/DC Motor drives
- Various rectifiers
- DC supply for PWM inverter

V_{DRM}, V_{RRM}	Type & Outline		
	600V	800V	1000V
1200V	MTC110-06-224H3/224H3B	MTC110-08-224H3/224H3B	MTC110-10-224H3/224H3B
1400V	MTC110-12-224H3/224H3B	MTC110-14-224H3/224H3B	MTC110-16-224H3/224H3B
1600V	MTC110-18-224H3/224H3B		
1800V			

SYMBOL	CHARACTERISTIC	TEST CONDITIONS	T_A (°C)	VALUE			UNIT		
				Min	Type	Max			
$I_{T(AV)}$	Mean on-state current	180° half sine wave 50Hz Single side cooled, $T_c=85^\circ\text{C}$	125			110	A		
$I_{T(RMS)}$	RMS on-state current							173	A
I_{DRM} I_{RRM}	Repetitive peak current	at V_{DRM} at V_{RRM}	125			20	mA		
I_{TSM}	Surge on-state current	10ms half sine wave $V_R=60\%V_{RRM}$	125			1.9	kA		
I^2t	I^2t for fusing coordination							20	$10^3\text{A}^2\text{s}$
V_{TO}	Threshold voltage		125			0.80	V		
r_T	On-state slope resistance							2.29	$\text{m}\Omega$
V_{TM}	Peak on-state voltage	$I_{TM}=330\text{A}$	25			1.80	V		
dv/dt	Critical rate of rise of off-state voltage	$V_{DM}=67\%V_{DRM}$	125			1000	$\text{V}/\mu\text{s}$		
di/dt	Critical rate of rise of on-state current	Gate source 1.5A $t_r \leq 0.5\mu\text{s}$ Repetitive	125			200	$\text{A}/\mu\text{s}$		
I_{GT}	Gate trigger current	$V_A=12\text{V}$, $I_A=1\text{A}$	25	30		200	mA		
V_{GT}	Gate trigger voltage					0.6		2.5	V
I_H	Holding current					10		250	mA
I_L	Latching current							1000	mA
V_{GD}	Non-trigger gate voltage	$V_{DM}=67\%V_{DRM}$	125			0.2	V		
$R_{th(j-c)}$	Thermal resistance Junction to case	Single side cooled per chip				0.25	$^\circ\text{C}/\text{W}$		
$R_{th(c-h)}$	Thermal resistance case to heatsink	Single side cooled per chip				0.15	$^\circ\text{C}/\text{W}$		
V_{iso}	Isolation voltage	50Hz, R.M.S, $t=1\text{min}$, $I_{iso}=1\text{mA}(\text{MAX})$		3000			V		
F_m	Thermal connection torque(M5)			2.5		4.0	$\text{N}\cdot\text{m}$		
	Mounting torque(M6)			4.5		6.0	$\text{N}\cdot\text{m}$		
T_{vj}	Junction temperature			-40		125	$^\circ\text{C}$		
T_{stg}	Stored temperature			-40		125	$^\circ\text{C}$		
W_t	Weight				100		g		
Outline		224H3、224H3B							

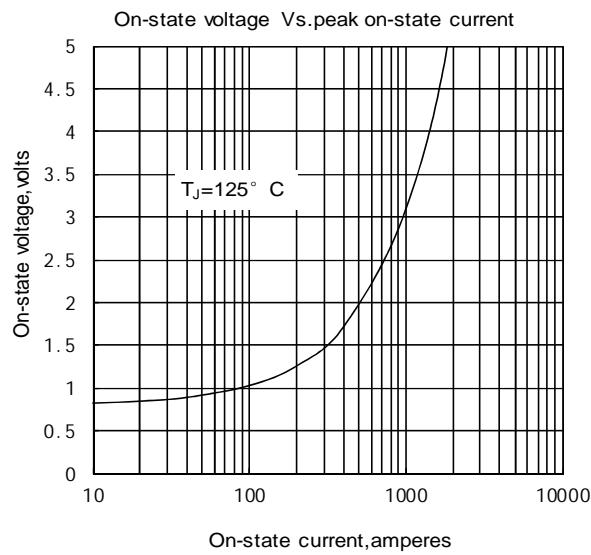


Fig1

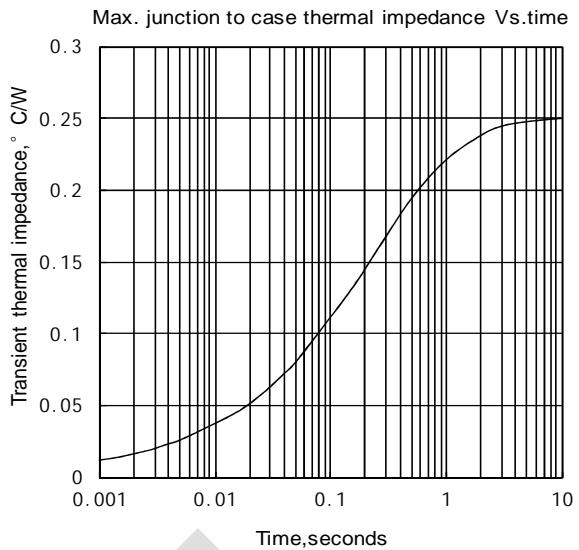


Fig2

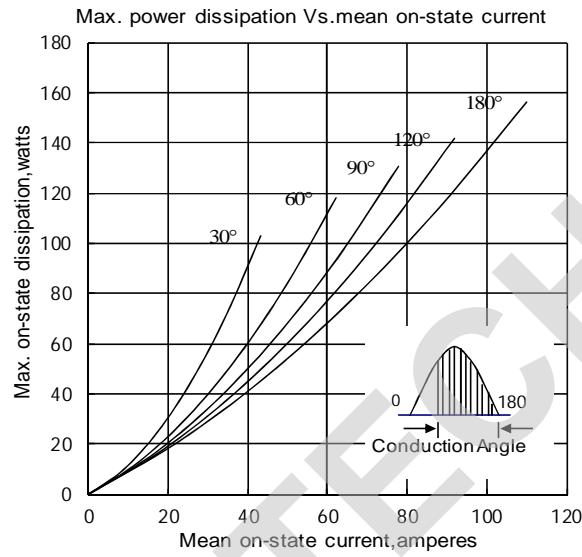


Fig3

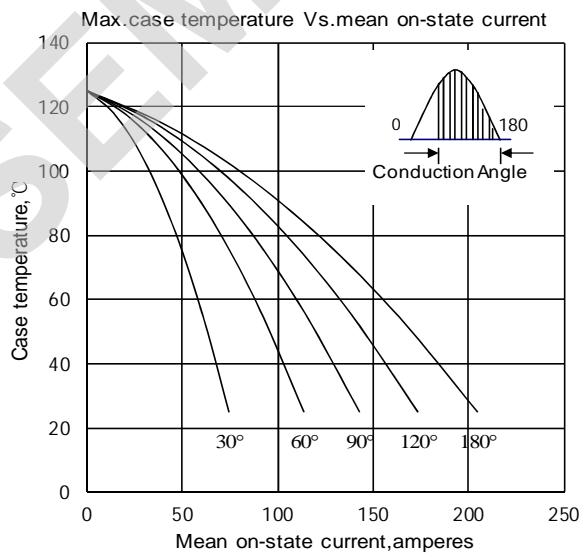


Fig4

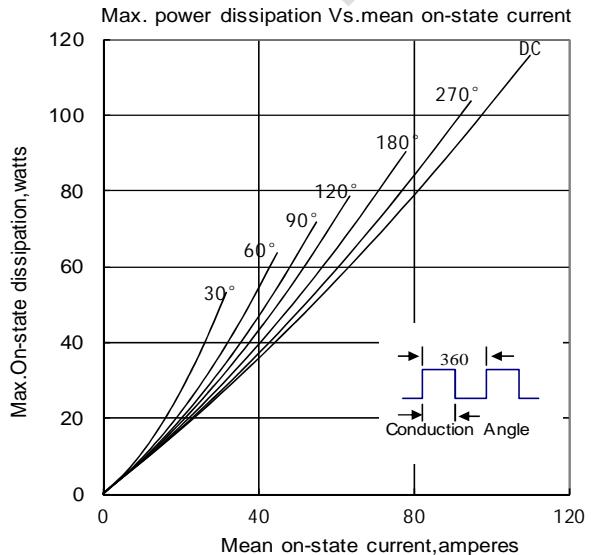


Fig5

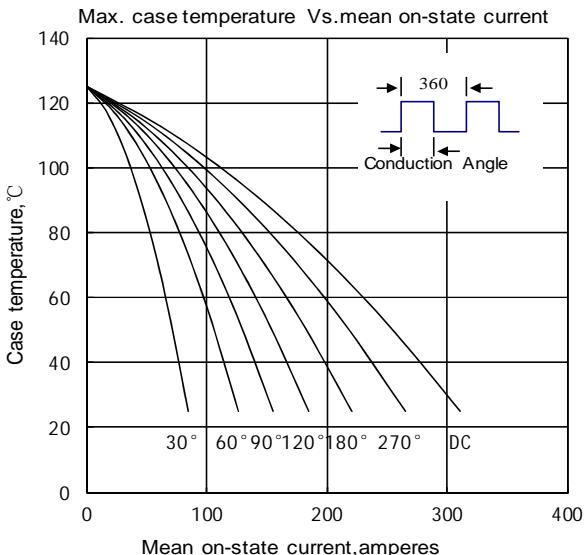


Fig6

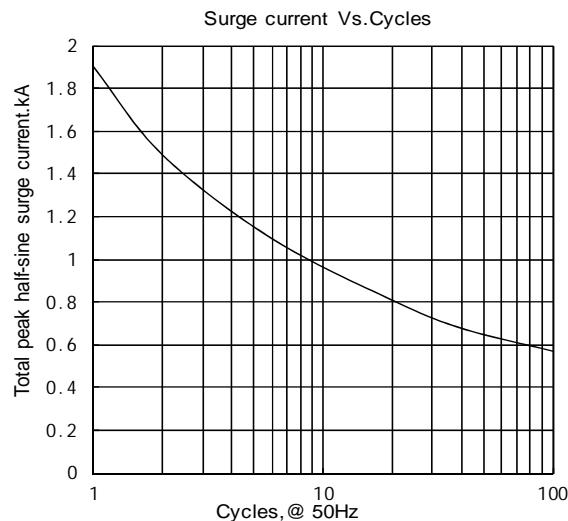


Fig7

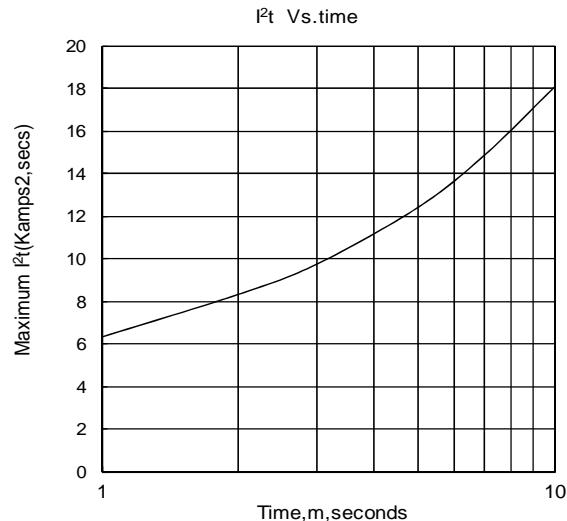


Fig8

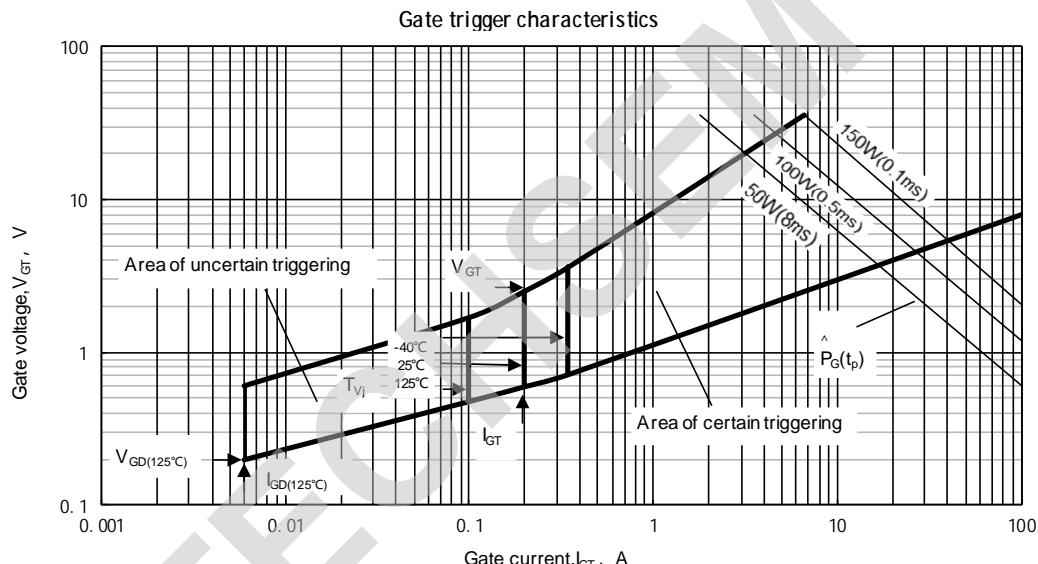
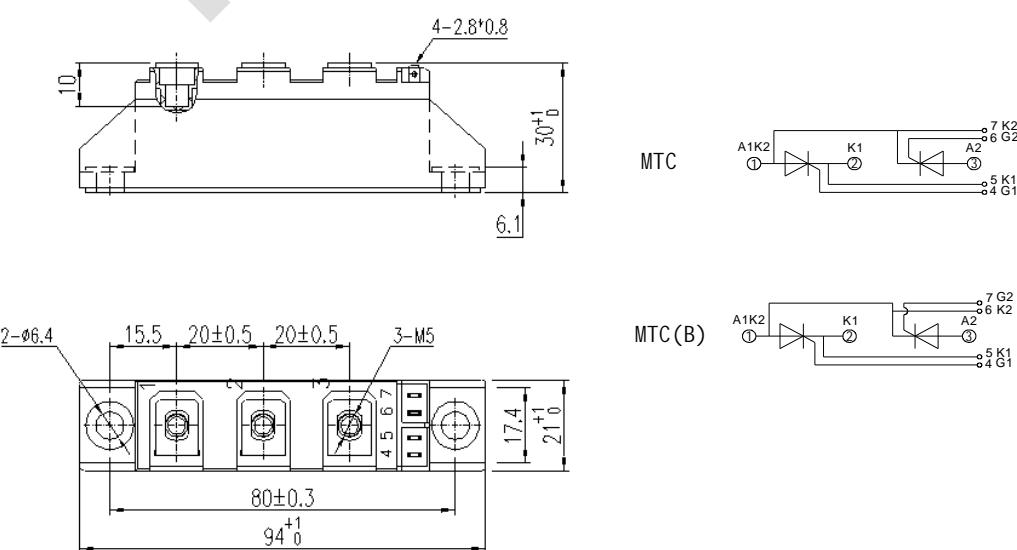


Fig.9

Outline:Unmarked dimensional tolerance: $\pm 0.5\text{mm}$

TECHSEM reserves the right to change specifications without notice.